A1015GR

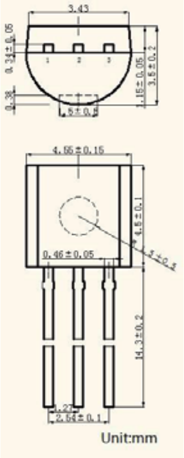
TRANSISTOR(PNP)

FEATURES

Power dissipation

MAXIMUM RATINGS(TA=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.15	A
P_D	Collector Power Dissipation	0.4	W
T_J	Junction Temperature	150	℃
T_{Stg}	Storage Temperature	-55-150	℃



1. EMITTER
2. COLLECTOR
3. BASE

ELECTRICAL CHARACTERISTICS(Ta=25℃ unless otherwise specified):

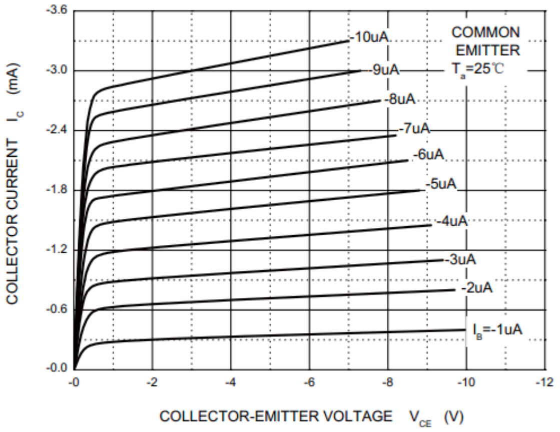
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	IC=-100uA, IE=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	IC=-1mA, IB=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	IC=-100uA, IC=0	-5			V
Collector cut-off current	I_{CBO}	VCB=-50V, IE=0			-100	nA
Collector cut-off current	I_{CEO}	VCE=-50V, IB=0			-100	nA
Emitter cut-off current	I_{EBO}	VEB=-5V，IC=0			-100	nA
DC current gain	$H_{FE(1)}$	V_{CE}=-6V，Ic=-2mA	70		400	
	$H_{FE(2)}$	V_{CE}=-6V，Ic=-150mA	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	IC=-100mA, IB=-10mA			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	IC=-100mA, IB=-10mA			-1.1	V
Gain Bandwidth Product	fT	VCE=-10V,IC=-1mA,f=30MHz	80			MHz
Collector output capacitance	Cob	VCB=-10V,IE=0,f=1MHZ			7	pF
Noise figure	NF	VCE=-6V,IC=-0.1mA,f=1KHz RG=10KΩ			6	dB

CLASSIFICATION OF $H_{FE(1)}$

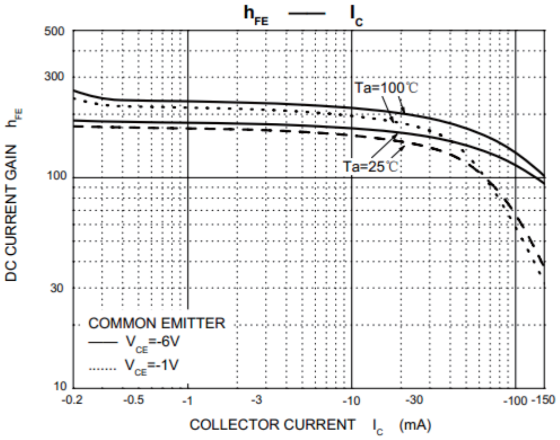
RANK	O	Y	GR
RANGE	70-140	120-240	200-400

Typical Characteristics

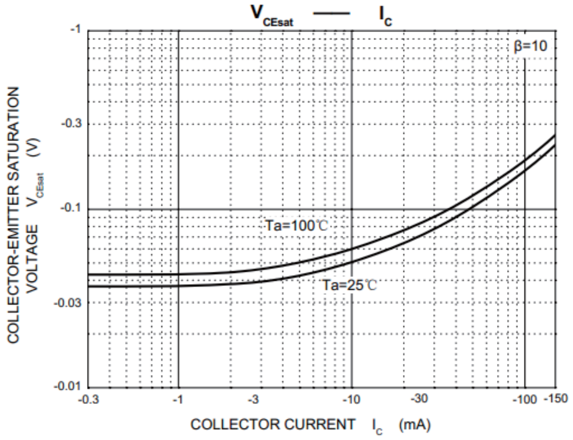
Static Characteristic



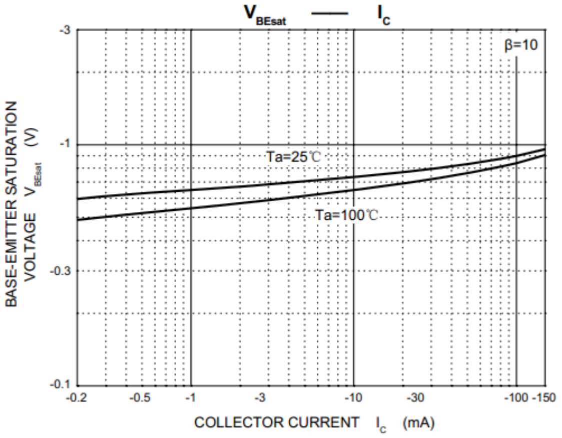
h_{FE} — I_C



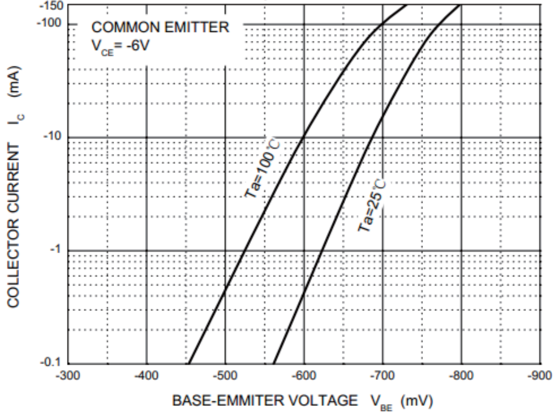
V_{CEsat} — I_C



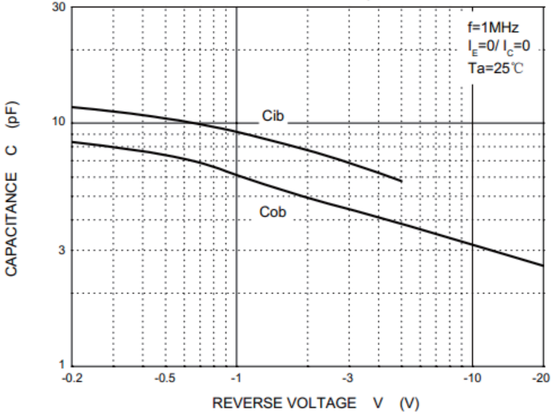
V_{BEsat} — I_C



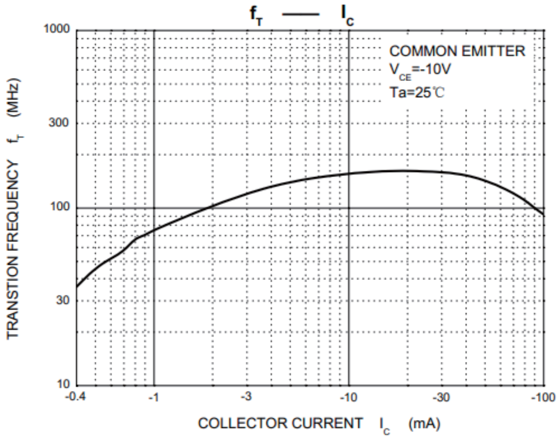
I_C — V_{BE}



C_{ob}/ C_{ib} — V_{CB}/ V_{EB}



f_T — I_C



P_C — T_a